



Scanning Electron Microscope (SEM) in situ field emission measurement in Uppsala Univ.





Tomoko Muranaka CERN, Switzerland 25 October 2012, LCWS12

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Background

Location: Developments & Experiments in Uppsala Univ. (UU).

Motivation: CLIC feasibility study / fundamental interest of understanding FE and BD phenomena, of material science.

Purpose: Find dependencies (field, time, gap, geometry, material, treatment, ..., crystal orientation,...)

Speciality 1: Local filed emission and breakdown measurements inside an SEM.

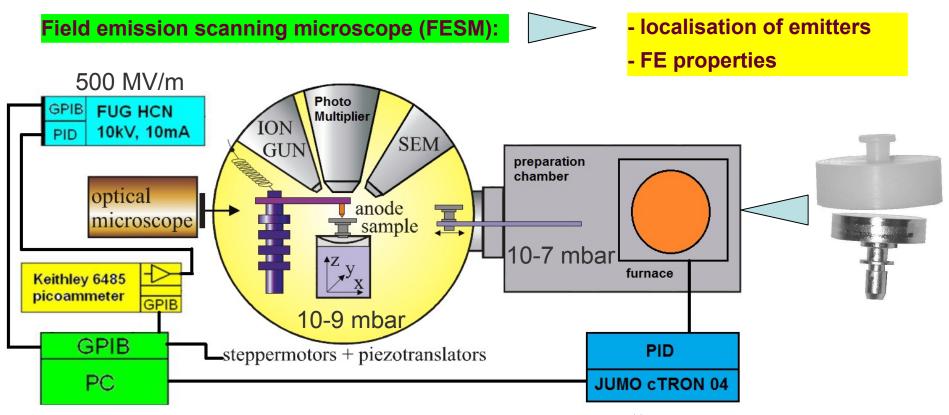
Speciality 2: Post-breakdown surface & sub-surface analyses by Focused Ion Beam (FIB) and SEM.

Ideas - What we can do

Speciality 1: Local filed emission and breakdown measurements inside an SEM.

- Reproduce high-gradient electric field condition in μm range (1kV/μm = 1GV/m)
- 2D scan with controlled gap distance.
- Measurement and observations in one instrument.
- Compact & transportable experimental setup.
- Complementary work with Wuppertal Univ.

Courtesy of Stefan Lagotzky, Günter Müller, Berg. Universität Wuppertal FE & SEM measurement techniques



- Spatially resolved I(E) measurements of single emitters Ŭ Eon, βFN, S
- $^{\circ}$ Ion bombardment (**Ar**, Eion= 0 − 5 kV) and SEM (low res.)
- In-situ heat treatments up to 1000°C

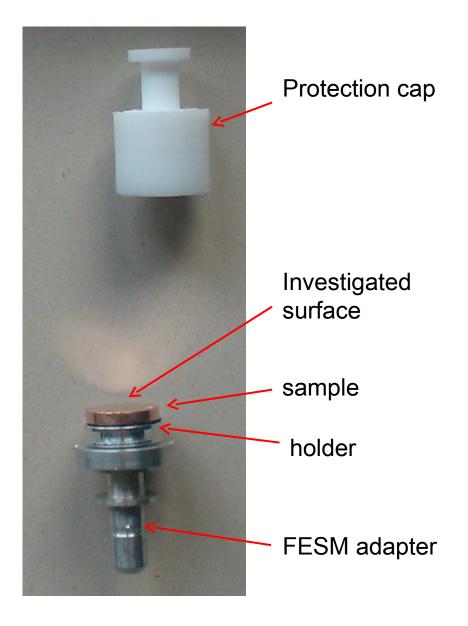
Ex-situ SEM + EDX



Identification of emitting defects

Correlation of surface features to FE properties (positioning accuracy ~ ±100 μm)

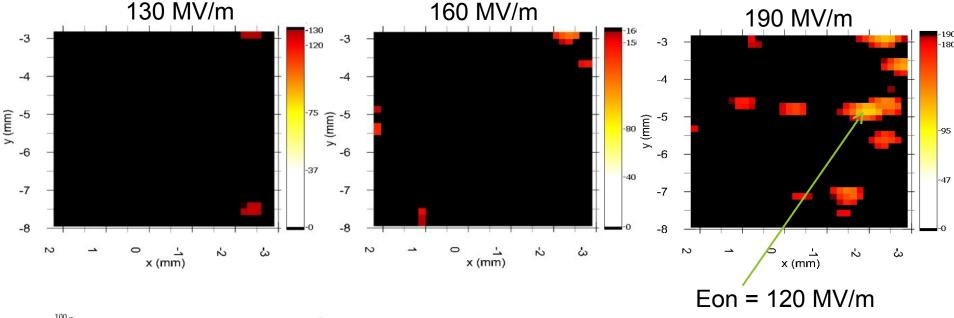
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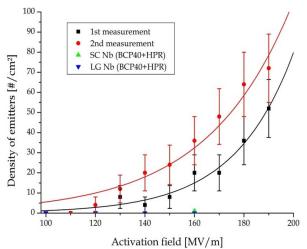


- Two flat Cu samples
- Diameter: ~11 mm
- One hole as mark to identify the position in different systems
- Diamond turned and glued to a sample holder at CERN
- Mounted to an adapter for the FESM at BUW
- Surface cleaned with ionized N2, cleanroom condition (class 100) with 5 bar pressure
- Teflon protection cap to avoid damage and contaminations after polishing and cleaning
- Only 1 sample measured yet

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Regulated E(x,y) maps for I = 1 nA , $\Delta z \approx 50 \ \mu m$ of the same area





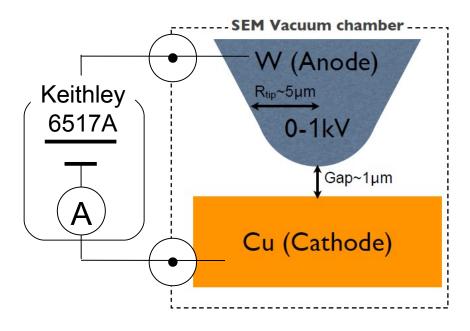
EFE starts at 130MV/m and not 500MV/m

- Emitter density increases exponentially with field
- Activated emitters: Eact=(1,2 1,4)·Eon
- 2nd measurement: shifted to lower fields

Possible explanations:

- Surface oxide
- adsorbates

Experiment setup in UU



- Cathode: Cu samples provided by CERN, 12mm-D, XY-stage
- Anode: W tip commercially available, 5µm-R, Z-stage
- Gap: $1.0 \pm 0.1 \, \mu m$
- Background current ≈0.02pA

SmarAct Piezo positionner http://www.smaract.de/

SLC-1720-S

Dimensions: 22 x 17 x 8.5 mm³

Travel: about 12 mmVelocity: up to 13 mm/s

Step width: 50 nm to 1000 nm

Scanning range: about 1.4 μm

Resolution: sub-nanometer

Blocking force: up to 3 N

Weight: about 13 g

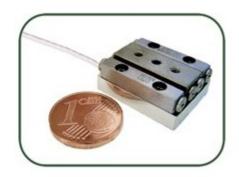
Allowable load: 40 N

Integrated nanosensor

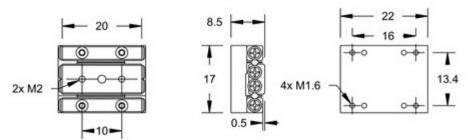
Options:

Vacuum compatibility: HV, UHV

Non-magnetic



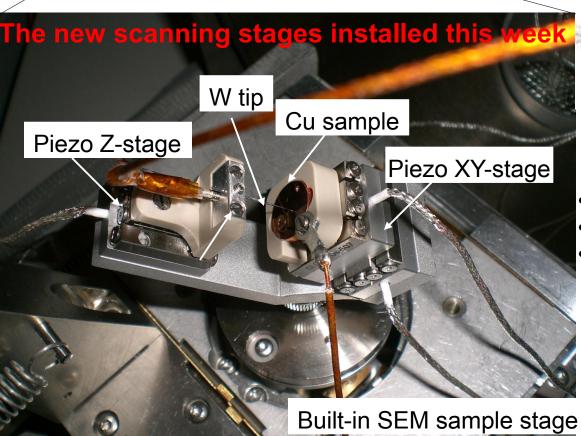
Drawing:

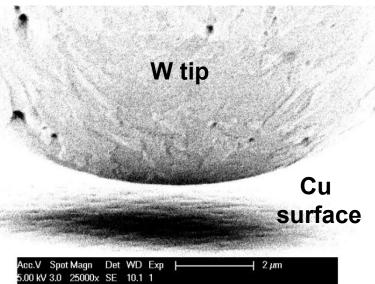


Linear dimensions are given in mm.



Real life



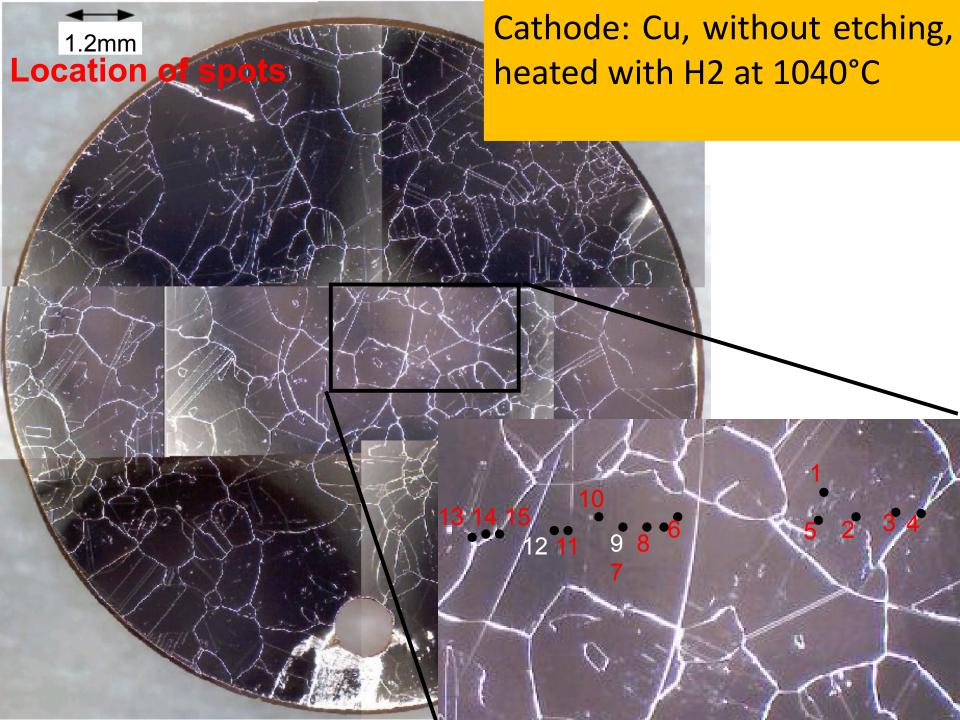


- Targeted scan
- Emission "SPOT" (≠area)
- Surface observation before&after

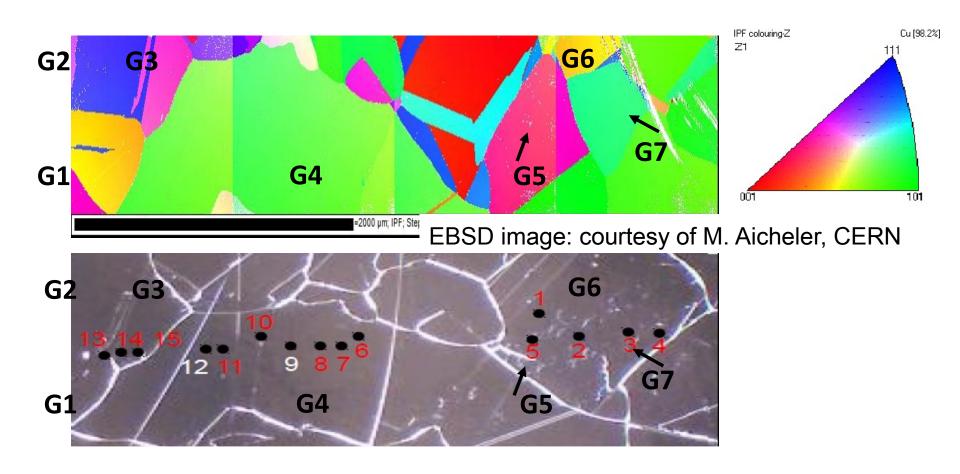
Example:

Grain orientation dependence (done with the old setup)

- 1. Approach W tip to the sample surface ~1µm
- 2. Take SEM images of target area
- 3. Apply HV on W tip from 0V up to 1kV with 1V step
- 4. Measure emission current from Cu sample
- 5. Stop HV supply once the current exceeds 10 nA (onset voltage)
- 6. Repeat 5 runs at the same spot
- 7. Move sliders to a new spot (blind)
- 8. Analyses: Comparison of onset voltage of each spots, Electron Backscatter Diffraction (EBSD) in order to identify grain orientations of spots.



Grain orientations of measured area



Grain orientation dependence



Summary

- The onset voltages where the measured current exceeded 10 nA were varied from 300 V to over 1000 V.
- The onset voltages were decreased at subsequent runs at most of spots (cf. Wuppertal's result).
- In order to study any dependences of emission behavior, more statistics are required.
- We are now almost ready to perform local field emission measurements with piezo scanners.

Co-workers

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Mechanical drawing and manufacture

Masih Noor

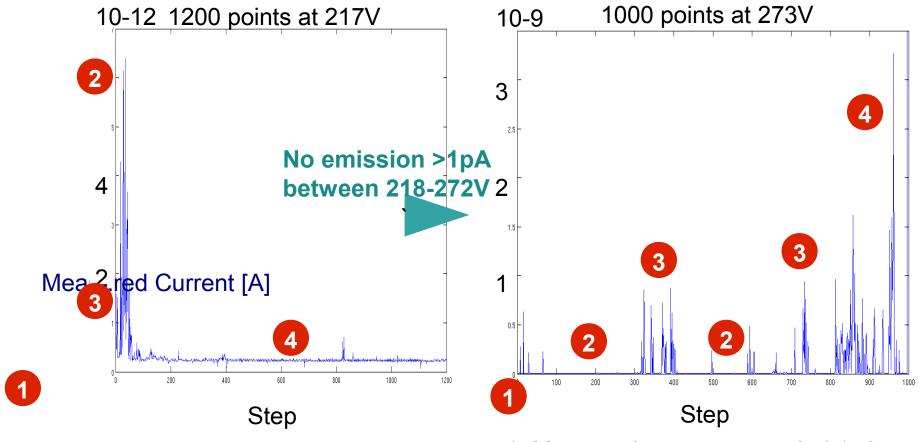
Lars-Erik Lindquist

Backups

Emission stability measurement

- 1. Approach W tip to the sample surface ~1µm
- 2. Take SEM images of target area
- 3. Apply HV on W tip from 0V up to 1kV with 1V step
- 4. Measure emission current from Cu sample
- 5. Once the measured current exceeds 1pA, keep the voltage and continue current measurement for 20 minutes
- 6. Repeat 3-5
- 7. Stop measurement once the measured current exceeds 10nA.

Emission stability measurement



- 1. Measured current exceeded 1pA
- 2. Up to 6 pA
- 3. Decreased to the bg-level
- 4. Stayed at the bg-level

- 1. Measured current exceeded 1pA
- 2. Decreased to the bg-level
- 3. Spikes ~1nA
- 5. Emissions > nA then exceeded 10nA

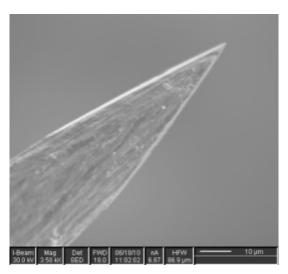
Summary: Emission stability

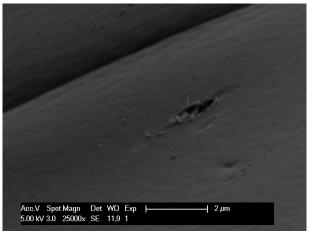
Spikes appeared and disappeared as if field emitters were growing and evaporating.

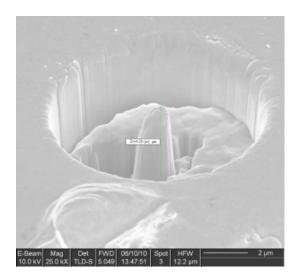
Still the tendency is that higher the E-field, higher the current.

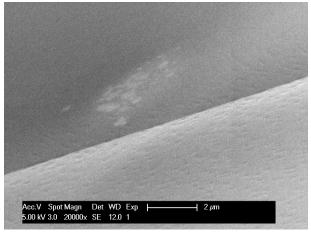
Macroscopic emission current that follows Fowler-Nordheim might be an average of (unstable) local emissions.

The assumption above could be tested by statistical measurements and/or measurements with anodes of various sizes.









Gap determination

- 1. Find a target site by approaching the tip to the surface with the SEM stage tilted 30 degrees.
- 2. Take the target site surface images at 0 degree. Low magnification images are used for finding the position on the surface and high magnification images are for comparing surface condition before/after measurements. (the tip should be retracted in order to avoid shadows)
- 3. Set the tip on the measurement position. The stage is tilted 30 degrees and rotated to be in a plane perpendicular to the SEM detector.
- 4. Comparing with a reference image and a marked transparent sheet, the gap can be set in less than 10% accuracy.





